TD5G10065A

Silicon Carbide Schottky Diode

V_{RRM}	=	650 V
I_F (T_C=153 ℃)	=	10 A
Q_C	=	36 nC

Features

- 650 V Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- High Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switching Mode Power Supply
- Boost Diodes in PFC
- DC/DC Converters
- AC/DC Converters
- Free Wheeling Diodes in Inverter

Package

TO-220-2

RoHS

Part Number	Package	Marking
TD5G10065A	TO-220-2	TD5G10065A

Maximum Ratings （Tc = 25 ℃ unless otherwise specified）

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	650	V		
V_{RSM}	Surge Peak Reverse Voltage	650	V		
V_R	DC Peak Reverse Voltage	650	V		
I_F	Continuous Forward Current	33 15 10	A	T_c=25 ℃ T_c=135 ℃ T_c=153 ℃	Fig. 3
I_{FSM}	Non-Repetitive Forward Surge Current	80	A	T_c=25 ℃，t_p=10 ms，Half Sine Pulse	
P_{tot}	Power Dissipation	117 50	W	T_c=25 ℃ T_c=110 ℃	Fig. 4
T_J	Operating Junction Range	-55 to +175	℃		
T_{stg}	Storage Temperature Range	-55 to +175	℃		

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.4 1.65	1.7 2.2	V	I_F = 10 A， T_J = 25 ℃ I_F = 10 A， T_J = 175 ℃	Fig. 1
I_R	Reverse Current	2 10	50 200	μA	V_R = 650 V， T_J = 25 ℃ V_R = 650 V， T_J = 175 ℃	Fig. 2
Q_C	Total Capacitive Charge	36		nC	V_R = 400 V， I_F = 10 A， T_J = 25 ℃	Fig. 6
C	Total Capacitance	695 69 52		pF	V_R = 0 V， T_J = 25 ℃， f = 1 MHz V_R = 200 V， T_J = 25 ℃， f = 1 MHz V_R = 400 V， T_J = 25 ℃， f = 1 MHz	Fig. 5
E_C	Capacitance Stored Energy	4.6		μJ	V_R = 400 V	Fig. 7

Note：This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case		1.28		℃/W	Fig.8

Typical Performance

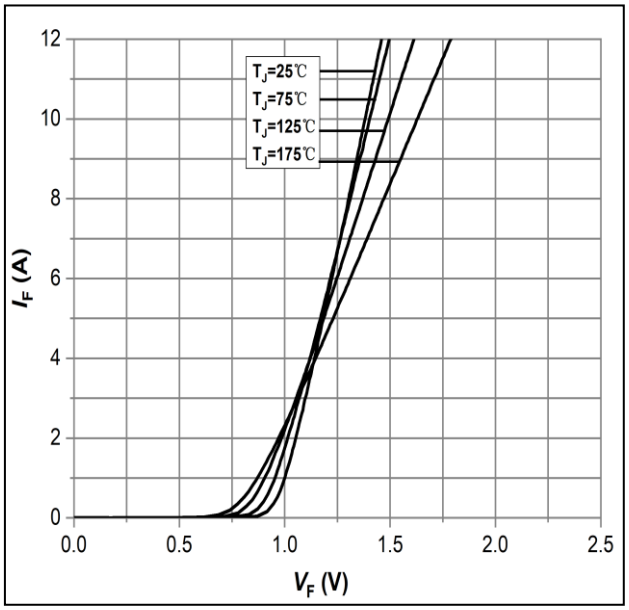


Figure 1: Forward Characteristics

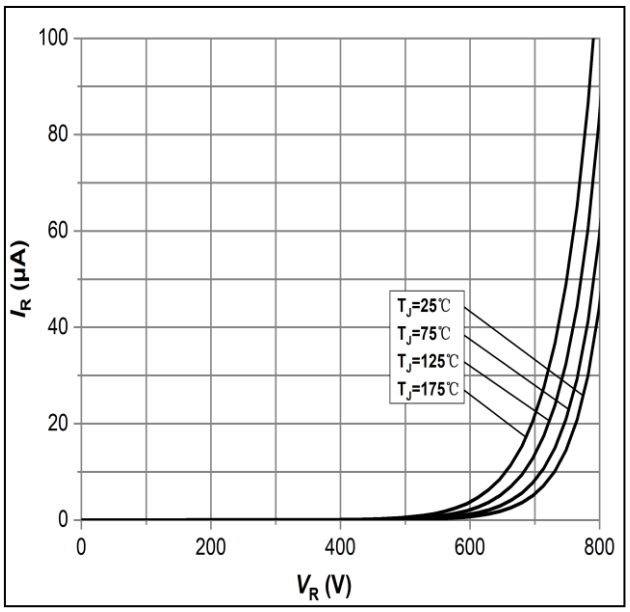


Figure 2: Reverse Characteristics

Typical Performance

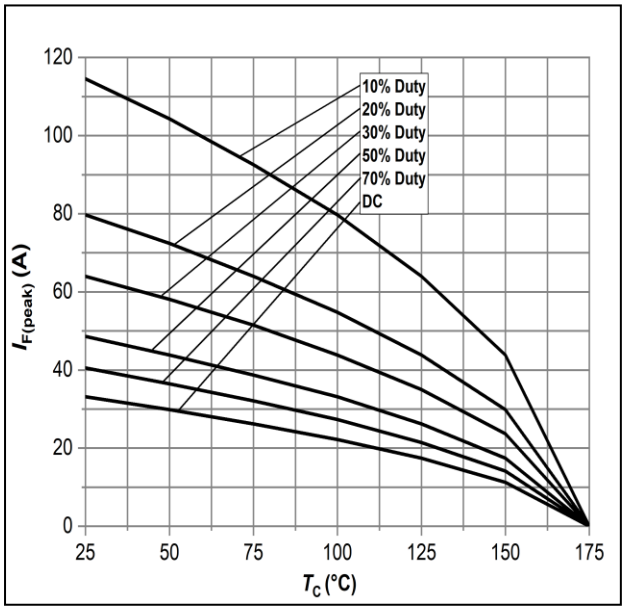


Figure 3: Current Derating

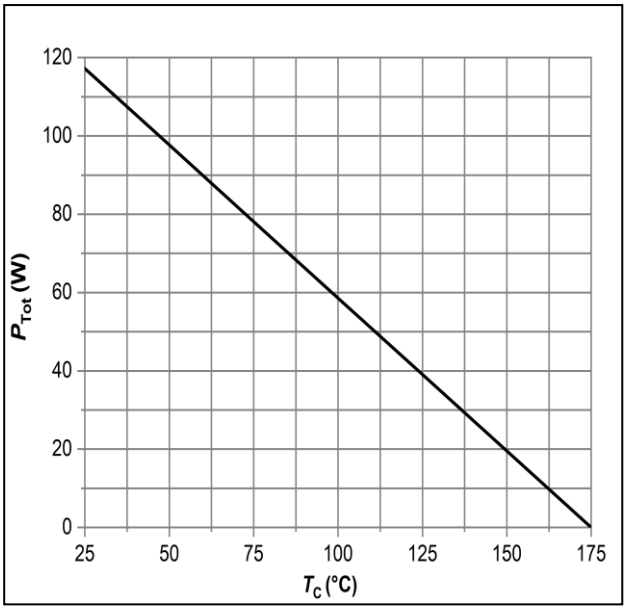


Figure 4: Power Derating

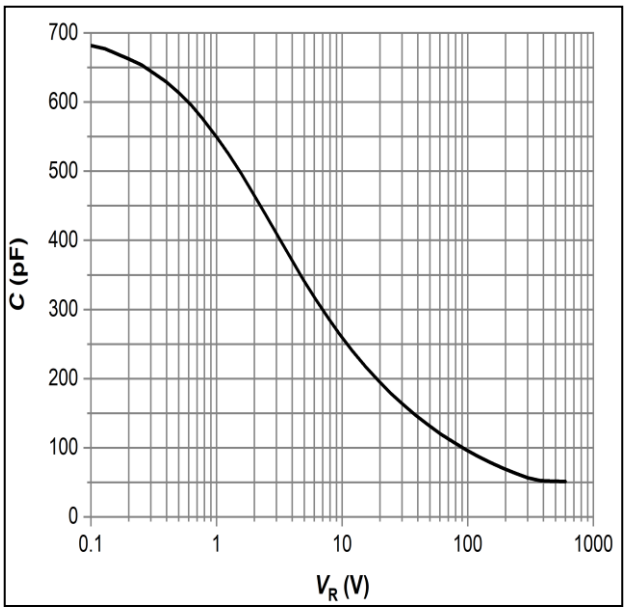


Figure 5: Capacitance vs. Reverse Voltage

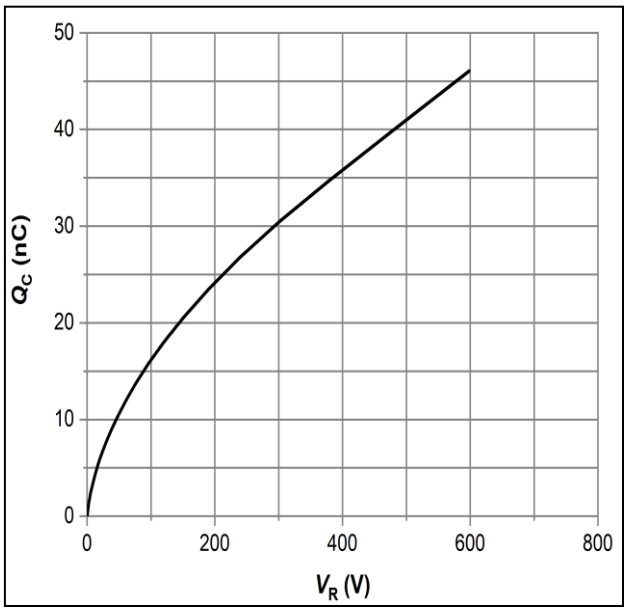


Figure 6: Total Capacitance Charge vs. Reverse Voltage

Typical Performance

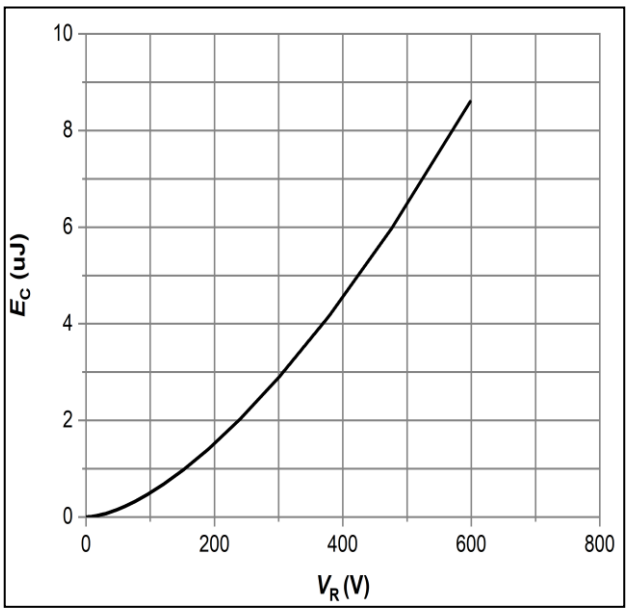


Figure 7:Typical Capacitance Stored Energy

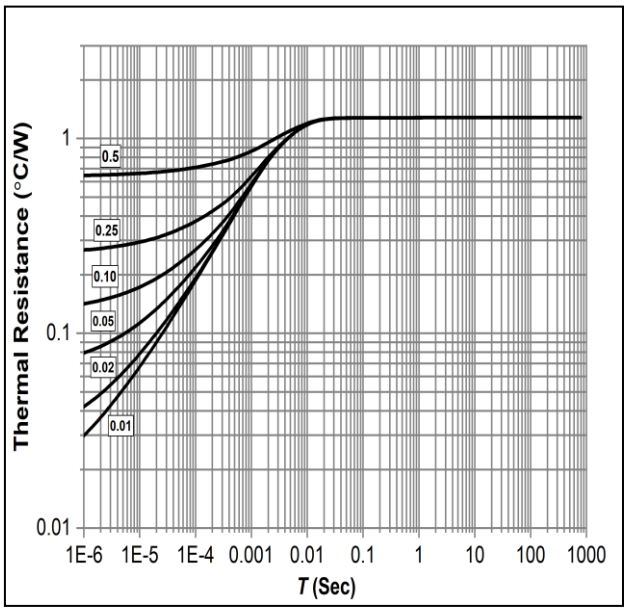
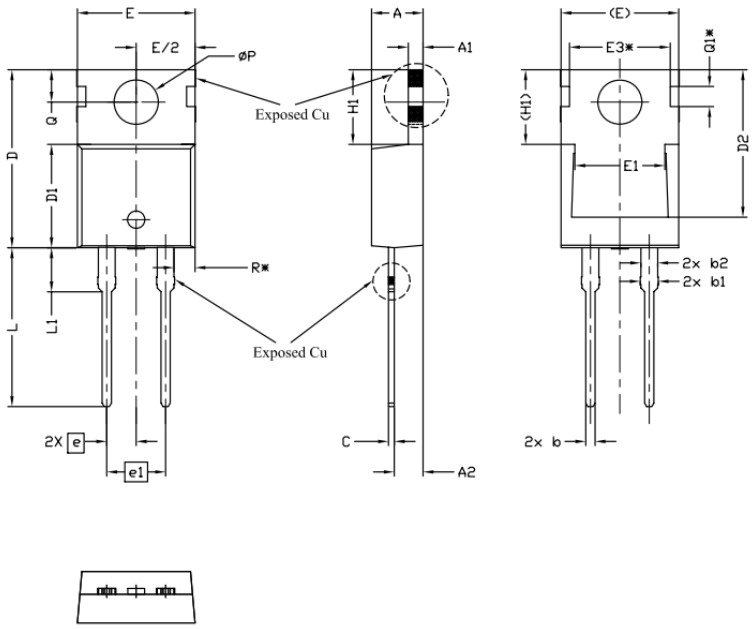


Figure 8: Transient Thermal Impedance

Package Dimensions

Package： TO-220-2



SYMBOL	DIMENSIONS			NOTES
	Min.	NOM	Max.	
A	4.24	4.44	4.64	
A1	1.15	1.27	1.40	
A2	2.30	2.48	2.70	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
c	0.40	0.50	0.60	
D	14.70	15.37	16.00	4
D1	8.82	8.92	9.02	
D2	12.43	12.73	12.83	5
E	9.96	10.16	10.36	4.5
E1	6.86	7.77	8.89	5
E3*	8.70 REF			
e	2.54 BSC			
e1	5.08 BSC			
H1	6.30	6.45	6.60	5.6
L	13.47	13.72	13.97	
L1	3.60	3.80	4.00	
ØP	3.75	3.84	3.93	
Q	2.60	2.80	3.00	
Q1*	1.73 REF			
R*	1.82 REF			

NOTE : Dimension L, M, W apply for Solder Dip Finish

Revision History

Document Version	Description of Changes
Rev.1.0	Released

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